



YJD65G10B

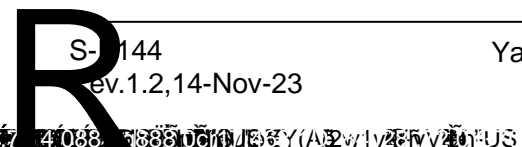
N-Channel Enhancement Mode FET

Product

V_{DS}

I_D

$R_{DS(ON)}$





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Electrical Characteristics ($T_j=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250$				



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Typical Performance Characteristics

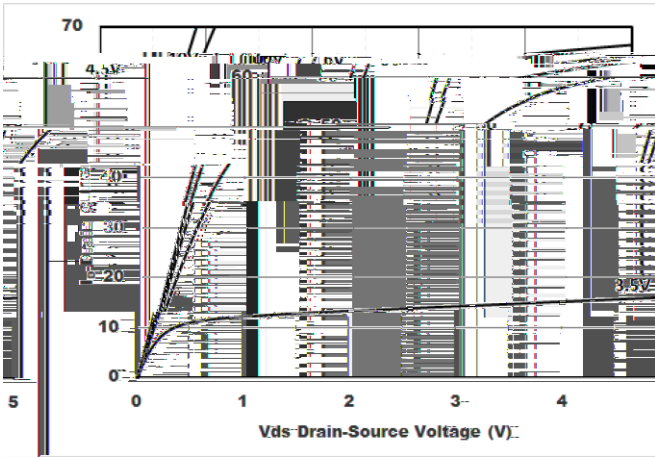


Figure1. Output Characteristics

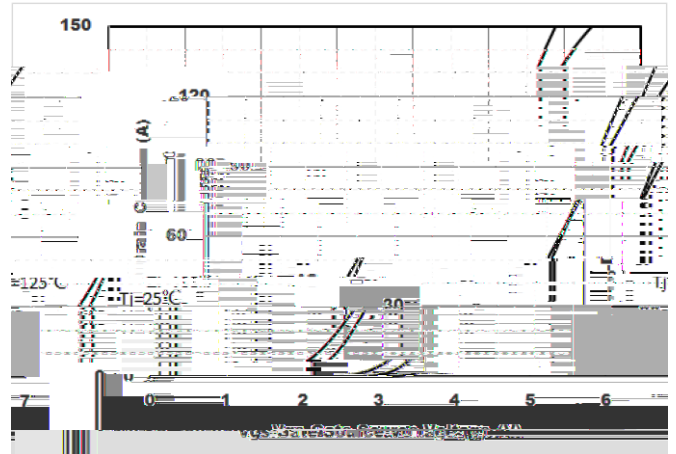


Figure2. Transfer Characteristics

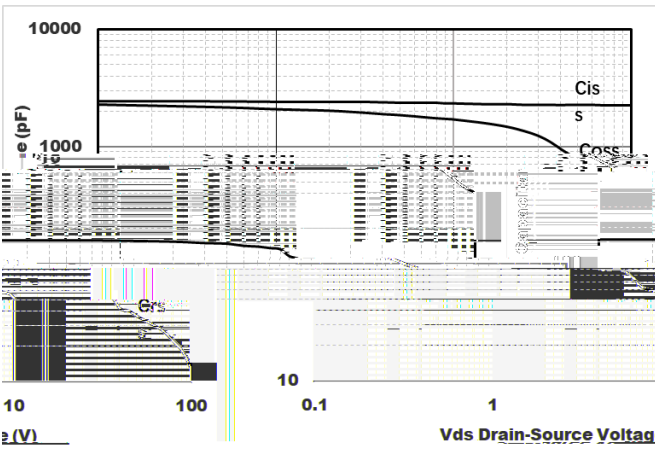


Figure3. Capacitance Characteristics

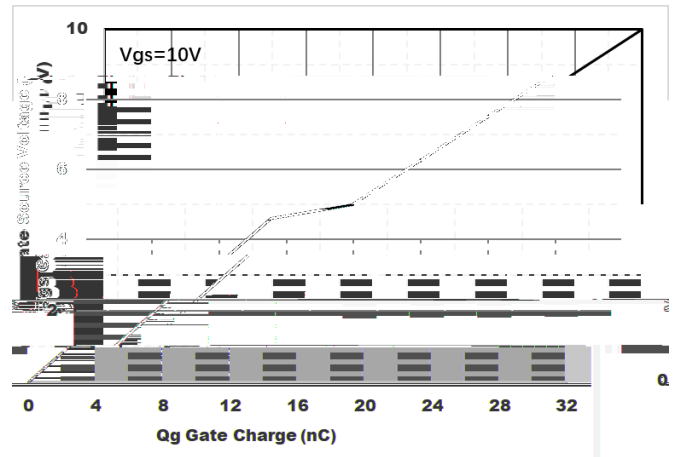


Figure4. Gate Charge

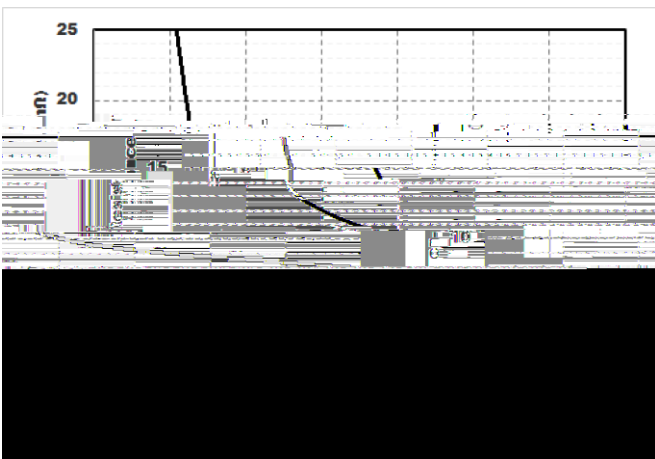


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

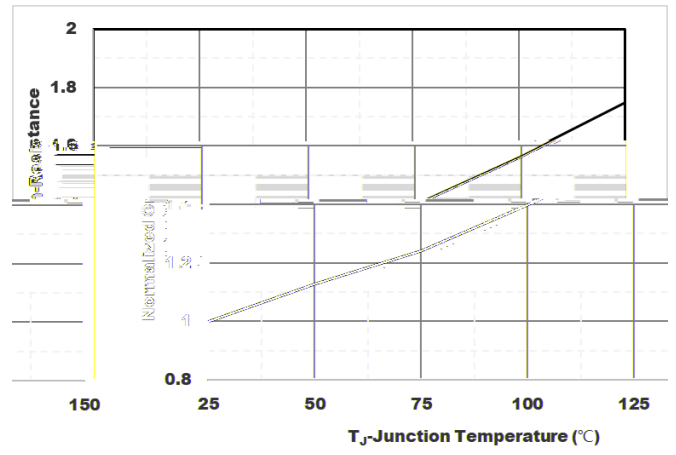


Figure6. Normalized On-Resistance



Figure7. Drain current

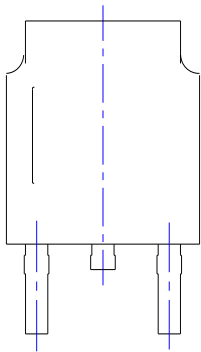
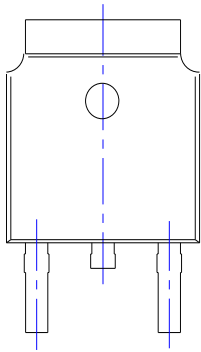
Figure8.Safe Operation Area

Figure9.Normalmalmalmalm4Q&Wvqg€;250Y+10stvExY;25AF



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TO-252-B Package information



DIMENSIONS				
SYMBOL	INCHES			
	MIN.	NOM.		
A1	0.000			
A2	0.087	0.091		
A3	0.035	0.039		
b	0.026	0.030		
c	0.018	0.020		
D	0.256	0.260		
D1				
D2	0.181	0.189		
E	0.390	0.398		
E1	0.236	0.240		

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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